SI3900DV-T1-E3-VB Datasheet

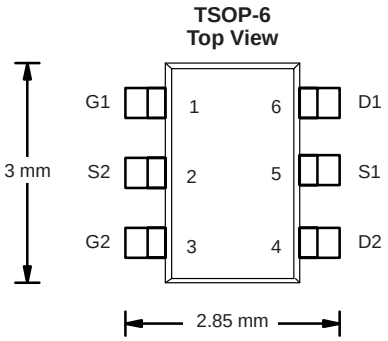
Dual N-Channel 20 V (D-S) MOSFET

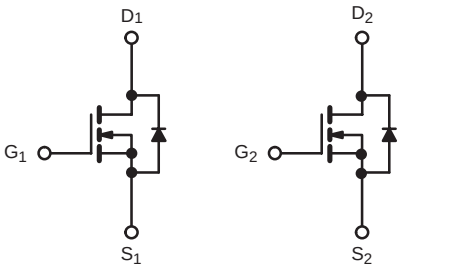
PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
20	0.022 at V_{GS} = 4.5 V	6.0	1.8 nC
	0.028 at V_{GS} = 2.5 V	5.0	

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- Trench Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT





N-Channel MOSFET N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	6.0	A
	T_C = 70 °C		4.0	
	T_A = 25 °C		3.5[b, c]	
	T_A = 70 °C		2.8[b, c]	
Pulsed Drain Current		I_{DM}	18	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	1.17	
	T_A = 25 °C		0.95[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	1.6	W
	T_C = 70 °C		1.0	
	T_A = 25 °C		1.14[b, c]	
	T_A = 70 °C		0.73[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)[d, e]			260	

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[b, d]	t ≤ 5 s	R_{thJA}	93	110	°C/W
Maximum Junction-to-Foot	Steady State	R_{thJF}	75	90	

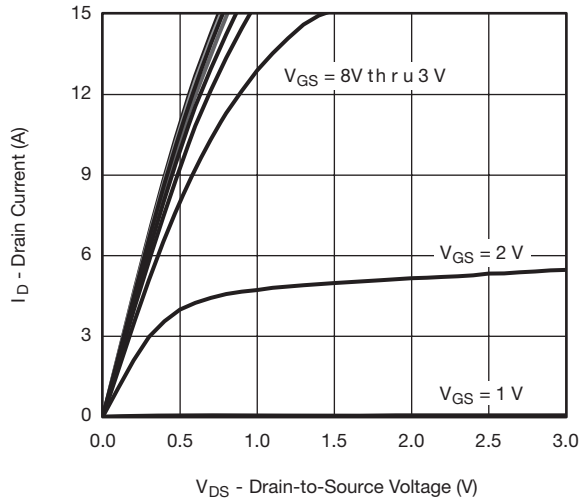
Notes:
a. T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. Maximum under steady state conditions is 150 °C/W.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		29		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 4		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 250 µA	0.4		1.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	10			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 3.4 A		0.022		Ω
		V_{GS} = 2.5 V, I_D = 3.0 A		0.028		
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 3.4 A		10		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz		400		pF
Output Capacitance	C_{oss}			55		
Reverse Transfer Capacitance	C_{rss}			26		
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 10 V, I_D = 3.4 A		3.7	6	nC
		V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 3.4 A		1.8	3	
Gate-Source Charge	Q_{gs}			0.74		
Gate-Drain Charge	Q_{gd}			0.42		
Gate Resistance	R_g	f = 1 MHz	1	5	10	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 5.6 Ω $I_D \cong$ 2.7 A, V_{GEN} = 4.5 V, R_g = 1 Ω		10	20	ns
Rise Time	t_r			15	30	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	t_f			10	20	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 5.6 Ω $I_D \cong$ 2.7 A, V_{GEN} = 10 V, R_g = 1 Ω		5	10	
Rise Time	t_r			15	30	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	t_f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C		1.2		A
Pulse Diode Forward Current	I_{SM}			18		
Body Diode Voltage	V_{SD}	I_S = 2.7 A, V_{GS} = 0 V		0.85	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 2.7 A, dI/dt = 100 A/µs, T_J = 25 °C		10	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}			4	10	nC
Reverse Recovery Fall Time	t_a			6		ns
Reverse Recovery Rise Time	t_b			4		

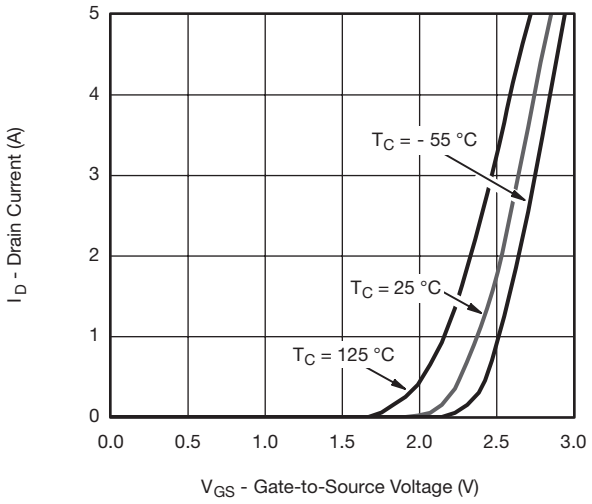
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

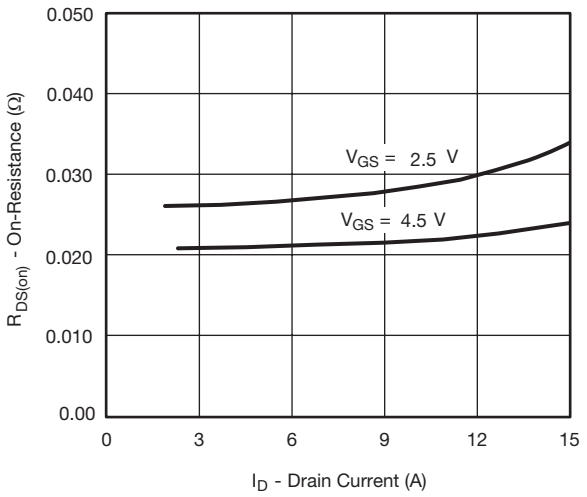
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



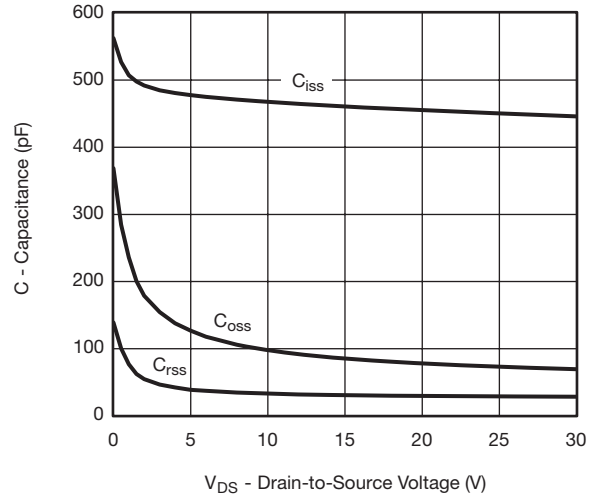
Output Characteristics



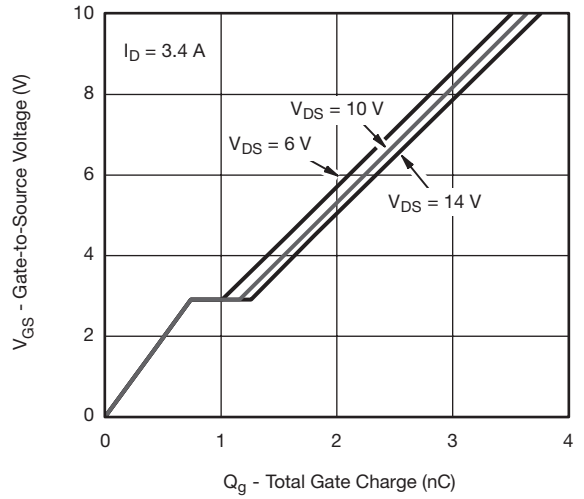
Transfer Characteristics



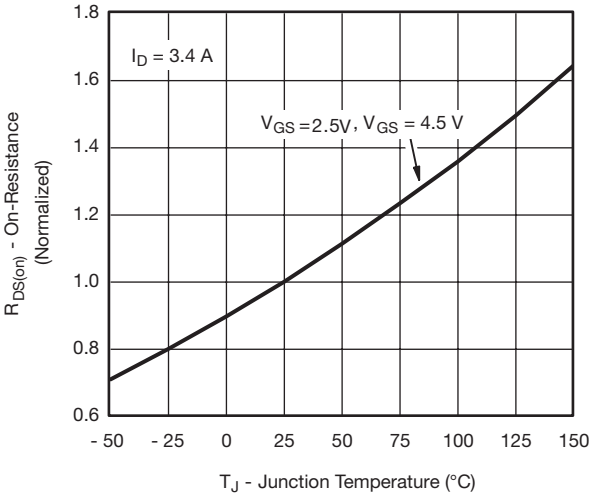
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

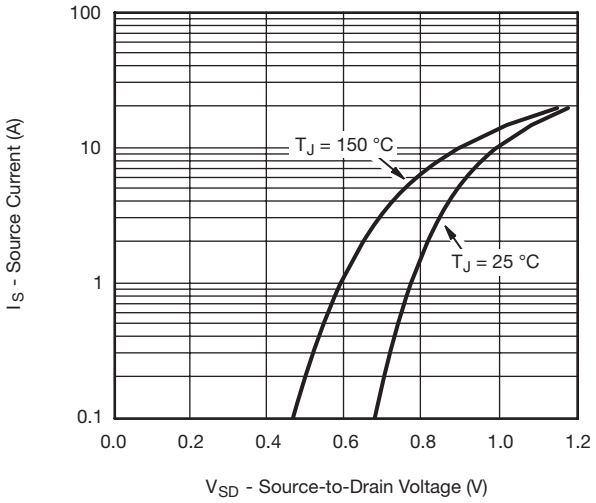


Gate Charge

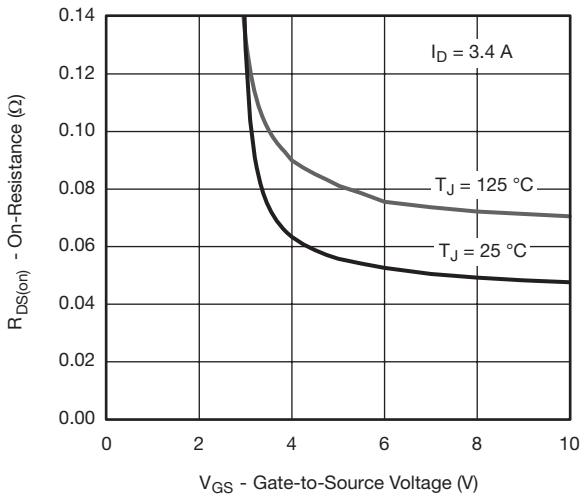


On-Resistance vs. Junction Temperature

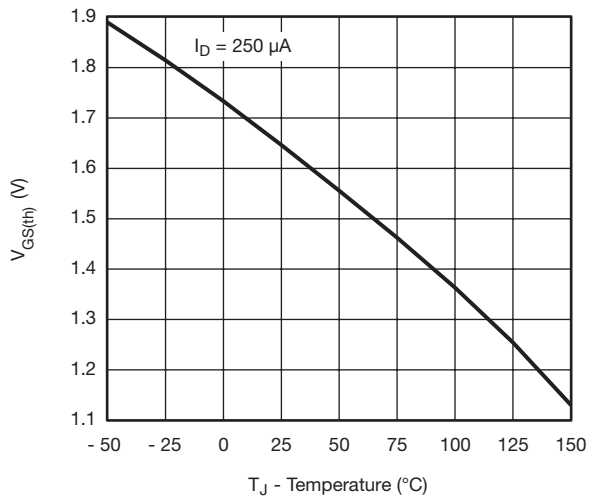
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



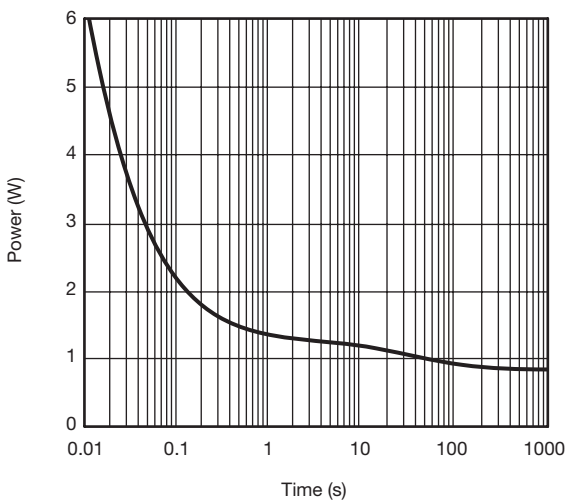
Source-Drain Diode Forward Voltage



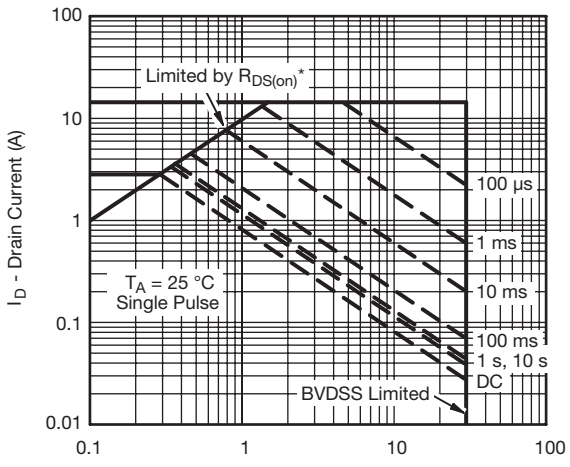
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



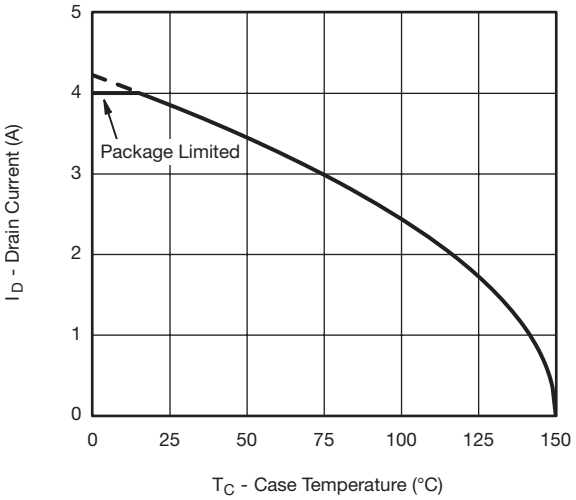
Single Pulse Power (Junction-to-Ambient)



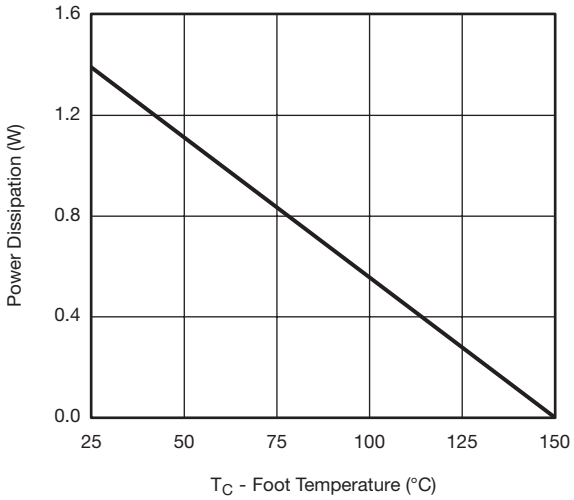
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



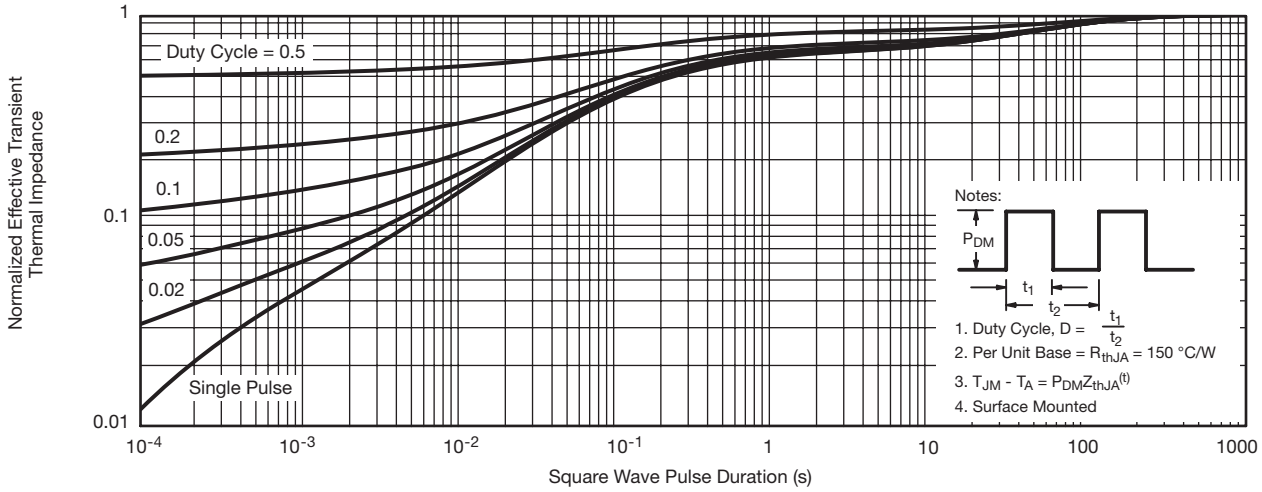
Current Derating*



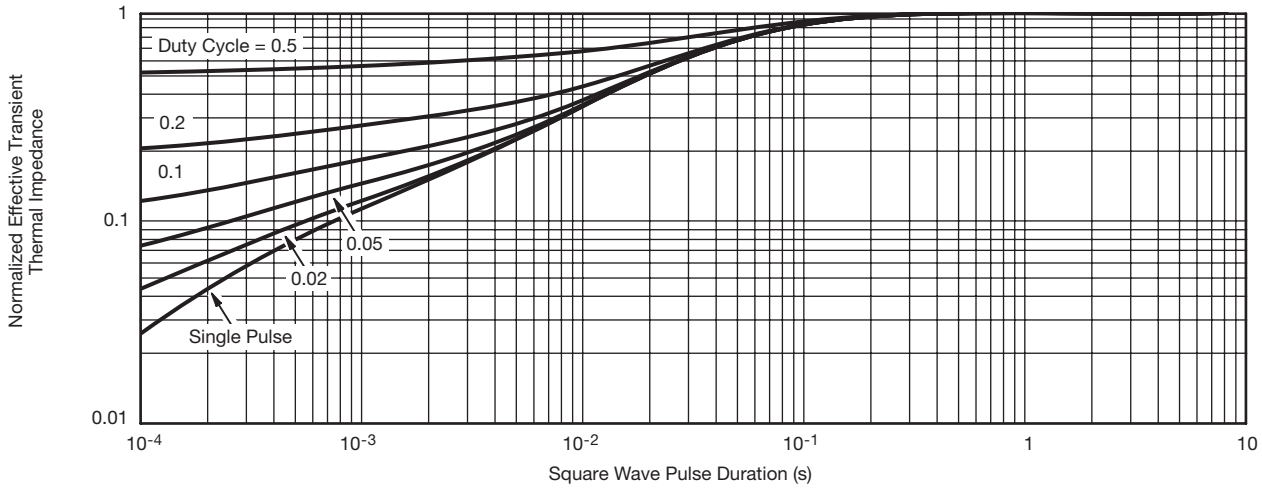
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

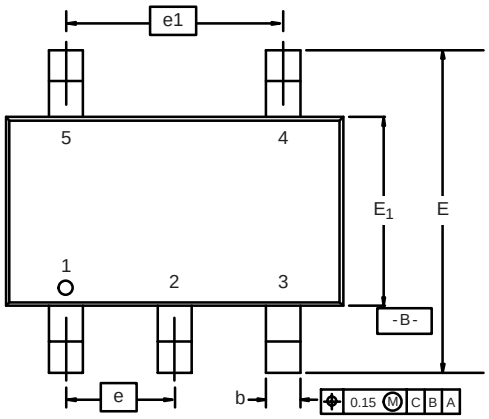


Normalized Thermal Transient Impedance, Junction-to-Ambient

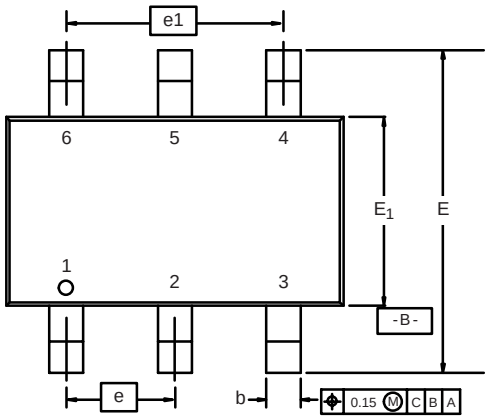


Normalized Thermal Transient Impedance, Junction-to-Foot

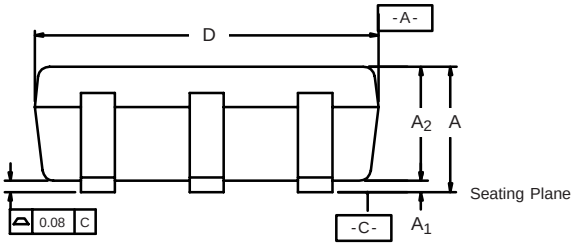
TSOP: 5/6−LEAD
JEDEC Part Number: MO-193C

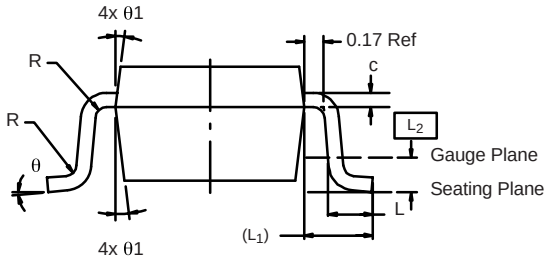


5-LEAD TSOP



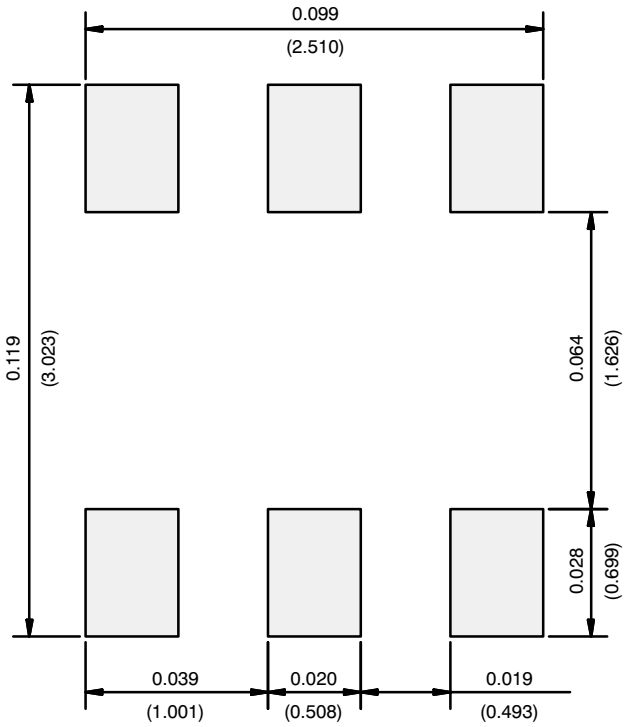
6-LEAD TSOP





Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A_1	0.01	-	0.10	0.0004	-	0.004
A_2	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E_1	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e_1	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L_1	0.60 Ref			0.024 Ref		
L_2	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
$θ_1$	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads
Dimensions in Inches/(mm)

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